

Shottky barrier diode

RB715W

●Application

Low current rectification

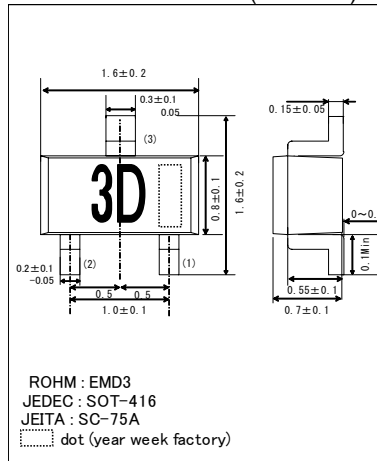
●Features

- 1) Ultra small mold type. (EMD3)
- 2) Low V_F
- 3) High reliability.

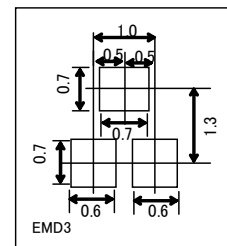
●Construction

Silicon epitaxial planer

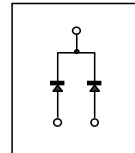
●External dimensions (Unit : mm)



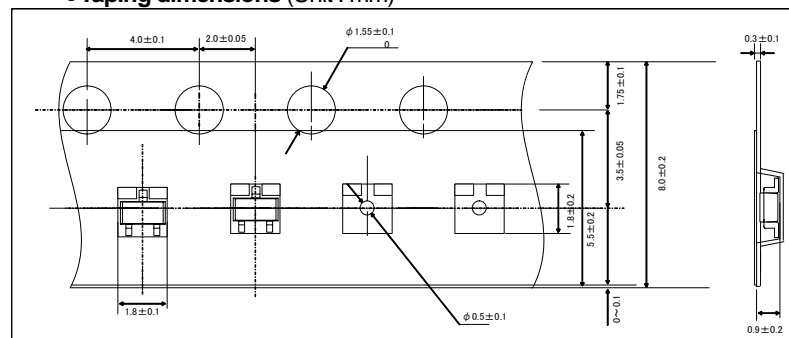
●Lead size figure (Unit : mm)



●Structure



●Taping dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current	I_o	30	mA
Forward current surge peak (60Hz · 1cyc) (*1)	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

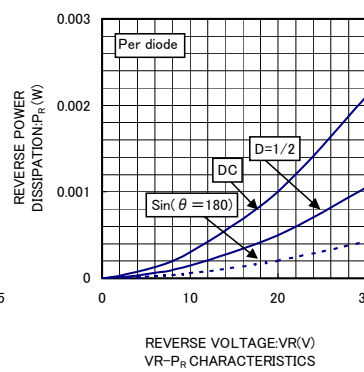
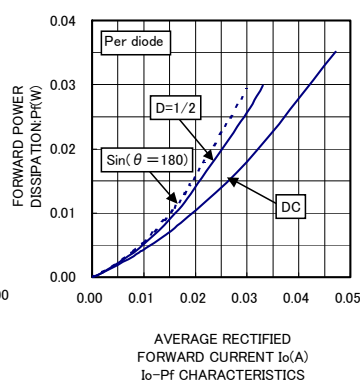
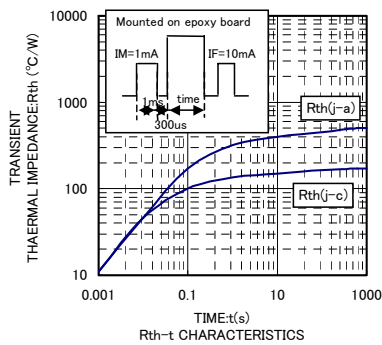
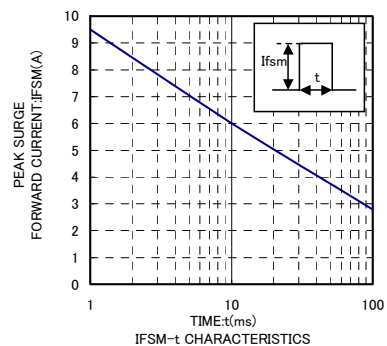
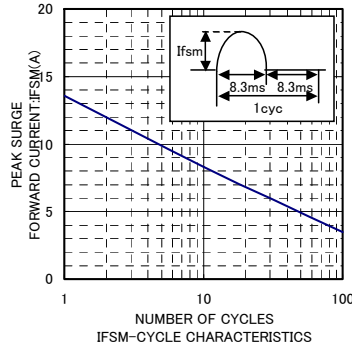
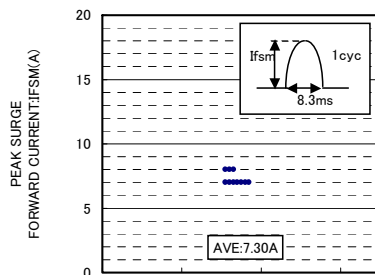
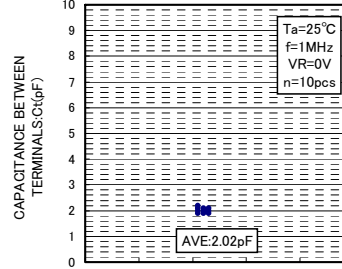
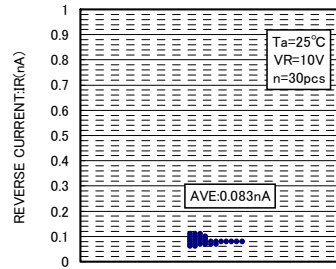
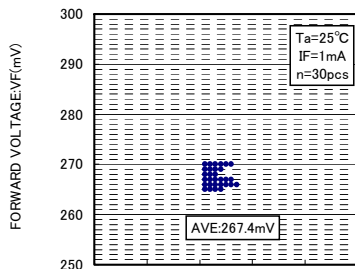
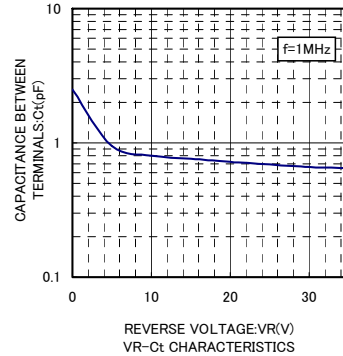
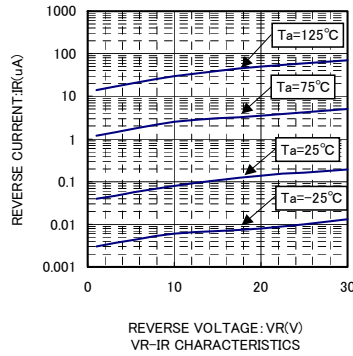
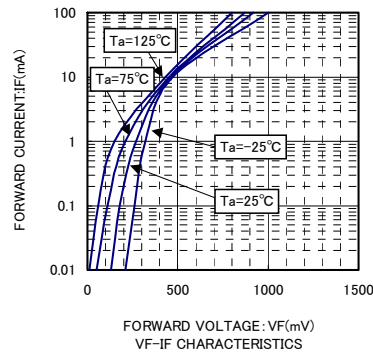
(*1)Rating of per diode

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.37	V	$I_F=1mA$
Reverse current	I_R	-	-	1	μA	$V_R=10V$
Capacitance between terminals	C_t	-	2.0	-	pF	$V_R=1.0V$ $f=1.0MHz$

Diodes

●Electrical characteristic curves (Ta=25°C)



Diodes

